AEGIS
SEMICONDUTORES LTDA.

A5A:1150.XX

VOLTAGE RATINGS

Part Number	V_{RRM} , V_R (V) Max. rep. peak reverse voltage		V_{RSM} , V_R (V) Max. non-rep. peak reverse voltage
	T_J = 0 to 175°C	T_J = -40 to 0°C	T_J = 25 to 175°C
A5A:1150.14	1400	1400	1500
A5A:1150.16	1600	1520	1700
A5A:1150.18	1800	1710	1900
A5A:1150.20	2000	1900	2100
A5A:1150.22	2200	2090	2300

MAXIMUM ALLOWABLE RATINGS

PARAMETER	VALUE	UNITS	NOTES
T_J Junction Temperature	-40 to 175	°C	-
T_{stg} Storage Temperature	-40 to 175	°C	-
$I_{F(AV)}$ Max. Av. current	960	A	180° half sine wave
@ Max. T_C	125	°C	
$I_{F(RMS)}$ Nom. RMS current	1800	A	-
I_{FSM} Max. Peak non-rep. surge current	12.2	kA	50 Hz half cycle sine wave; Initial T_J = 175° C, rated V_{RRM} applied after surge.
	12.8		60 Hz half cycle sine wave; Initial T_J = 175° C, rated V_{RRM} applied after surge.
	14.5		50 Hz half cycle sine wave; Initial T_J = 175°C, no voltage applied after surge.
	15.2		60 Hz half cycle sine wave; Initial T_J = 175°C, no voltage applied after surge.
I^2t Max. I^2t capability	627	kA^2s	t = 10ms; Initial T_J = 175°C, rated V_{RRM} applied after surge.
	683		t = 8.3 ms; Initial T_J = 175°C, rated V_{RRM} applied after surge.
	886		t = 10ms; Initial T_J = 175° C, no voltage applied after surge.
	966		t = 8.3 ms; Initial T_J = 175° C, no voltage applied after surge.
$I^2t^{1/2}$ Max. $I^2t^{1/2}$ capability	10600	$kA^2s^{1/2}$	Initial T_J = 175°C, no voltage applied after surge. I^2t for time $t_x = I^2t^{1/2} * t_x^{1/2}$. (0.1 < tx < 10ms).
F Mounting Force	900	N.m	-

AEGIS
SEMICONDUTORES LTDA.

A5A:1150.XX

CHARACTERISTICS

PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
V_{FM} Peak forward voltage	---	1.90	2.11	V	Initial T_J = 25 °C, 50-60Hz half sine, I_{peak} = 3016A.
$V_{F(TO)1}$ Low-level threshold	---	---	0.8	V	T_J = 175 °C
$V_{F(TO)2}$ High-level threshold	---	---	0.809		Av. power = $V_{F(TO)} * I_{F(AV)} + r_F * [I_{F(RMS)}]^2$
r_{F1} Low-level resistance	---	---	0.427	m	Use low values for I_{FM} < $I_{F(AV)}$
r_{F2} High-level resistance	---	---	0.396		
I_{RM} Peak reverse current	---	20	40	mA	TJ = 175°C. Max. Rated VRRM
R_{thJC} Thermal resistance, junction-to-case	---	---	0.038	°C/W	DC operation, double side
	---	---	0.045	°C/W	180° sine wave, double side
	---	---	0.046	°C/W	120° rectangular wave, duble side
R_{thCS} Thermal resistance, case-to-sink	---	---	0.02	°C/W	Mtg. Surface smooth, flat and greased. Double side.
wt Weight	---	85(3.0)	---	g(oz.)	---
Case Style	TO-200AB				---

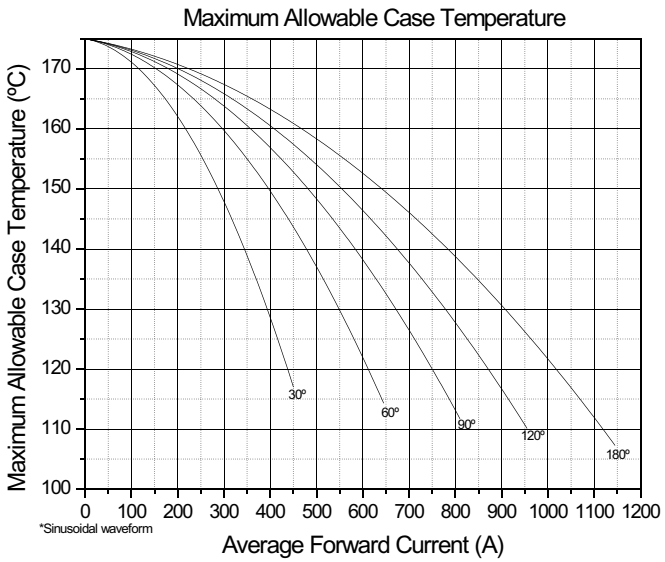

Fig. 1 - Current Ratings Characteristics

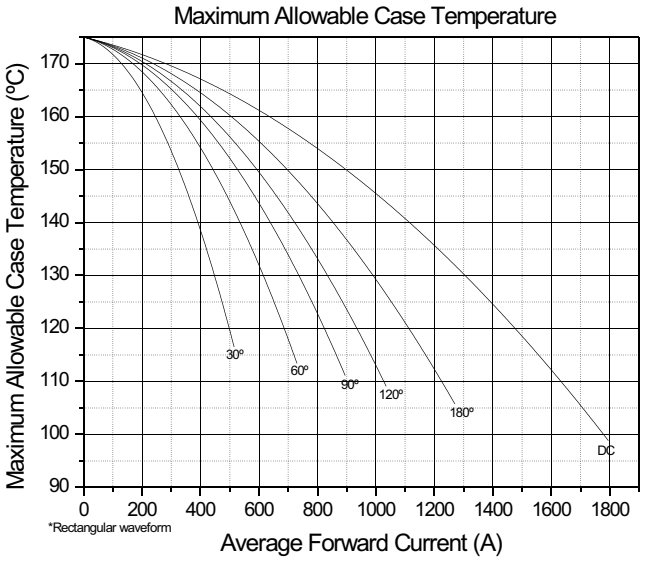

Fig. 2 - Current Ratings Characteristics

AEGIS
SEMICONDUTORES LTDA.

A5A:1150.XX

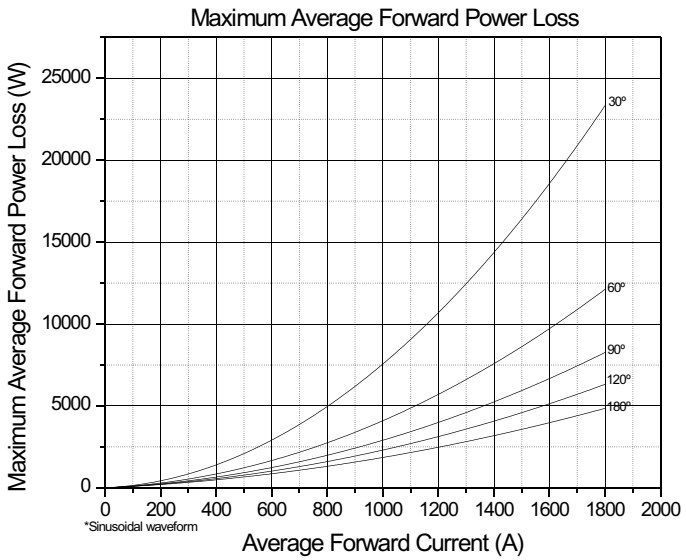

Fig. 3 - On-State Power Loss Characteristics

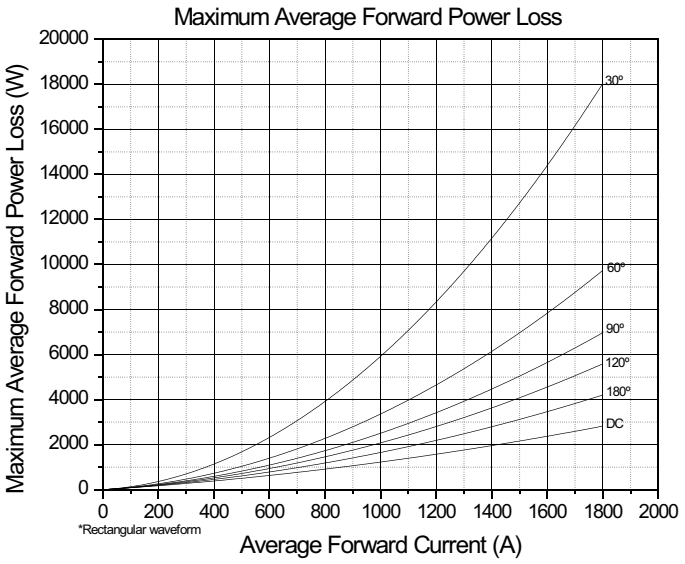

Fig. 4 - On-State Power Loss Characteristics

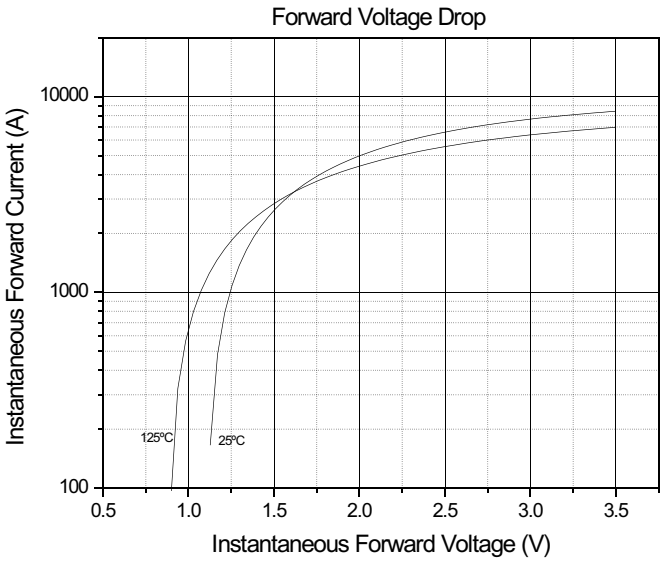

Fig. 5 - Forward Voltage Drop Characteristics

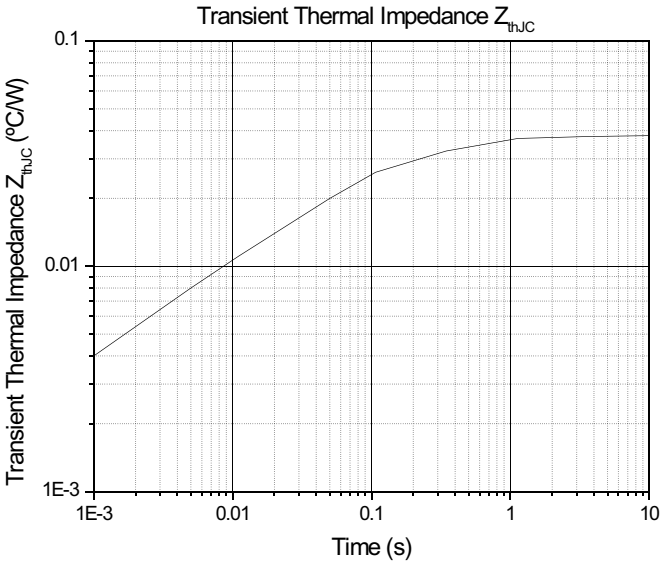

Fig. 6 - Transient Thermal Impedance Characteristics

AEGIS
SEMICONDUTORES LTDA.

A5A:1150.XX

TO-200AB

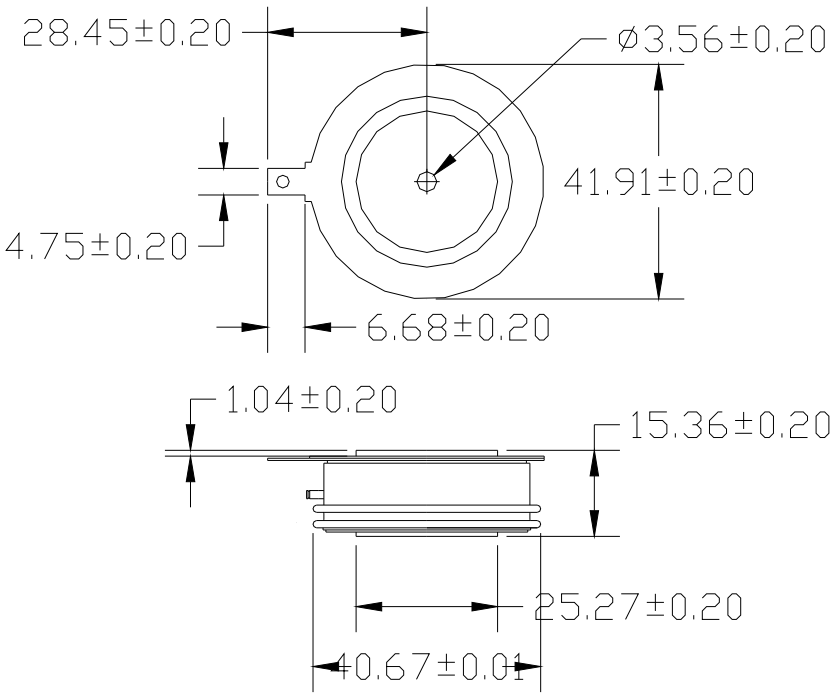

Fig. 7 - Outline Characteristics